

CLAIMS

1. A method of cleaning a heat treatment apparatus that deposits an SiO_2 film by means of TEOS on an object to be processed contained in a treatment vessel capable of forming a vacuum, the method comprising the step of:

cleaning the heat treatment apparatus by supplying an HF gas and an NH_3 gas into the treatment vessel.

2. The method of cleaning a heat treatment apparatus according to claim 1, wherein

during the cleaning step, a temperature in the treatment vessel is in a range of from 100°C to 300°C .

3. The method of cleaning a heat treatment apparatus according to claim 1 or 2, wherein

during the cleaning step, a pressure in the treatment vessel is equal to or more than 53200 Pa (400 Torr).

4. The method of cleaning a heat treatment apparatus according to any one of claims 1 to 3, wherein

during the cleaning step, a supply amount of the HF gas is equal to or more than a supply amount of the NH_3 gas.

5. A method of cleaning a heat treatment apparatus that deposits an AsSG film by means of TEOS on an object to be processed contained in a treatment vessel capable of forming a vacuum, the method comprising the step of:

cleaning the heat treatment apparatus by supplying an HF gas and an NH_3 gas into the treatment vessel.

6. A method of cleaning a heat treatment apparatus that deposits a BSG film by means of TEOS on an object to be processed contained in a treatment vessel capable of forming a vacuum, the method comprising the step of:

cleaning the heat treatment apparatus by supplying an HF gas and an NH_3 gas into the treatment vessel.